

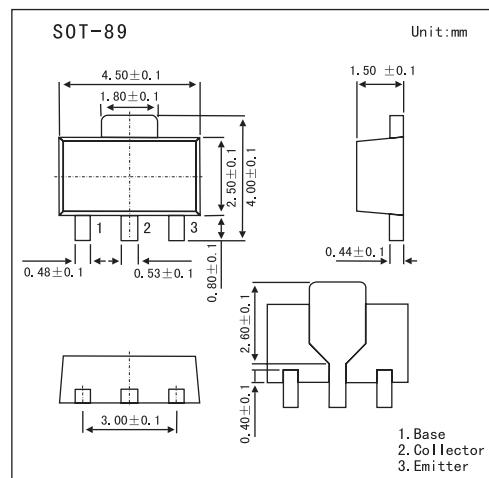
PNP Silicon Power Switching Transistor

FCX717

■ Features

- 2W power dissipation.
- 10A peak pulse current.
- Excellent HFE characteristics up to 10 Amps.
- Extremely low saturation voltage E.g. 12mv Typ.
- Extremely low equivalent on-resistance.

$R_{CE(sat)}$ 77mΩ at 3A.



■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

| Parameter | Symbol | Rating | Unit |
|---|----------------|-------------|------|
| Collector-base voltage | V_{CBO} | -12 | V |
| Collector-emitter voltage | V_{CEO} | -12 | V |
| Emitter-base voltage | V_{EBO} | -5 | V |
| Continuous collector current | I_{CM} | -10 | A |
| Peak pulse current | I_C | -3 | A |
| Base current | I_B | -500 | mA |
| Power dissipation | P_{tot} | 1 | W |
| Operating and storage temperature range | T_j, T_{stg} | -55 to +150 | °C |

FCX717■ Electrical Characteristics $T_a = 25^\circ C$

| Parameter | Symbol | Testconditons | Min | Typ | Max | Unit |
|---|---------------|--|-------------------------------|--------------------------------|-------|------|
| Collector-base breakdown voltage | $V_{(BR)CBO}$ | $I_C=-100\mu A$ | -12 | -35 | | V |
| Collector-emitter breakdown voltage * | $V_{(BR)CEO}$ | $I_C=-10mA$ | -12 | -25 | | V |
| Emitter-base breakdown voltage | $V_{(BR)EBO}$ | $I_E=-100\mu A$ | -5 | -8.5 | | V |
| Collector cut-off current | I_{CBO} | $V_{CB}=-10V$ | | | -100 | nA |
| Collector Emitter Cut-Off Current | I_{CES} | $V_{CE}=-10V$ | | | -100 | nA |
| Emitter Cut-Off Current | I_{EBO} | $V_{EB}=-4V$ | | | -100 | nA |
| Collector-emitter saturation voltage * | $V_{CE(sat)}$ | $I_C=-0.1A, I_B=-10mA$ $I_C=-1A, I_B=-10mA$ $I_C=-3A, I_B=-50mA$ | -12 -110 -230 | -20 -150 -320 | | mV |
| Base-emitter saturation voltage * | $V_{BE(sat)}$ | $I_C=-3A, I_B=-50mA$ | | -0.92 | -1.05 | V |
| Base-emitter ON voltage * | $V_{BE(on)}$ | $I_C=-3A, V_{CE}=-2V$ | | -0.85 | -1.0 | V |
| Static Forward Current Transfer Ratio * | h_{FE} | $I_C=-10mA, V_{CE}=-2V$ $I_C=-0.1A, V_{CE}=-2V$ $I_C=-3A, V_{CE}=-2V$ $I_C=-8A, V_{CE}=-2V$ $I_C=-10A, V_{CE}=-2V$ | 300 300 160 60 45 | 475 450 240 100 70 | | |
| Transitional frequency | f_T | $I_C=-50mA, V_{CE}=-10V, f=100MHz$ | 80 | 110 | | MHz |
| Output capacitance | C_{obo} | $V_{CB}=-10V, f=1MHz$ | | 21 | 30 | pF |
| Turn-on time | $t_{(on)}$ | $I_C=-2A, V_{CC}=-6V$ | | 70 | | ns |
| Turn-off time | $t_{(off)}$ | $I_{B1}=I_{B2}=50mA$ | | 130 | | ns |

* Pulse test: $t_p = 300 \mu s$; $d \leq 0.02$.

■ Marking

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| Marking | 717 |
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